TO-92 PNP Silicon PNP transistor in a TO-92 Plastic Package.

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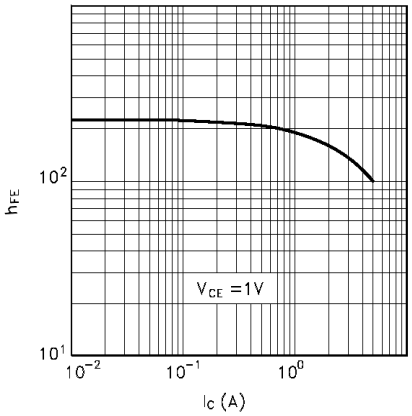
High I_C ,low $V_{CE(sat)}$.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-3.0	A
Peak Collector Current- Continuous	I_{CM}	-6.0	A
Collector Power Dissipation	P_C	0.9	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55˙ 150	

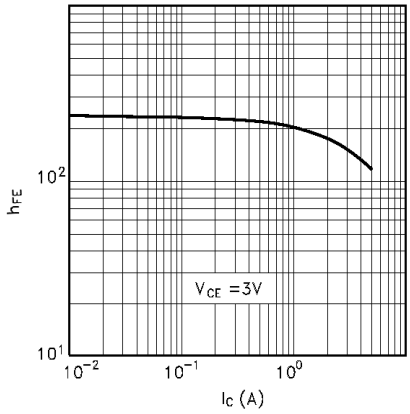
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-100μA I_E=0	-60			V
Collector to Emitter Breakdown Voltage*	*V_{CEO}	I_C=-10mA I_B=0	-60			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-100μA I_C=0	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-30V I_E=0			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-4.0V I_C=0			-1.0	μA
DC Current Gain	*$h_{FE(1)}$	V_{CE}=-2.0V I_C=-500mA	100	200	300	
	*$h_{FE(2)}$	V_{CE}=-2.0V I_C=-10mA	100	200		

/ Electrical Characteristic Curve

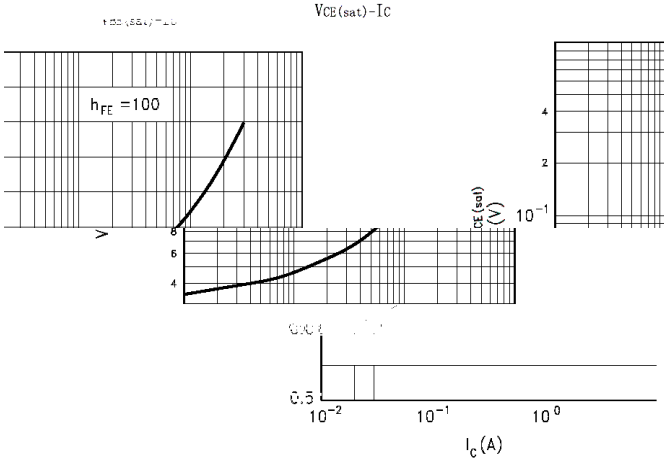
hFE-Ic

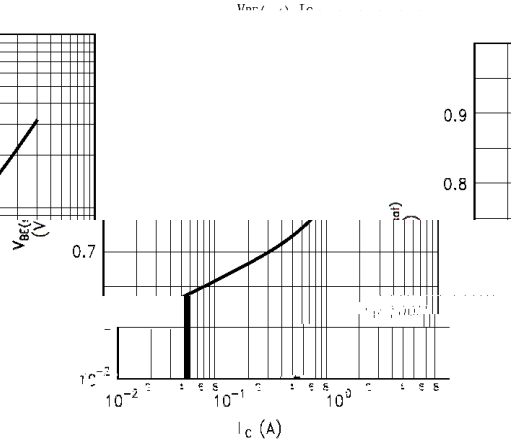


hFE-Ic

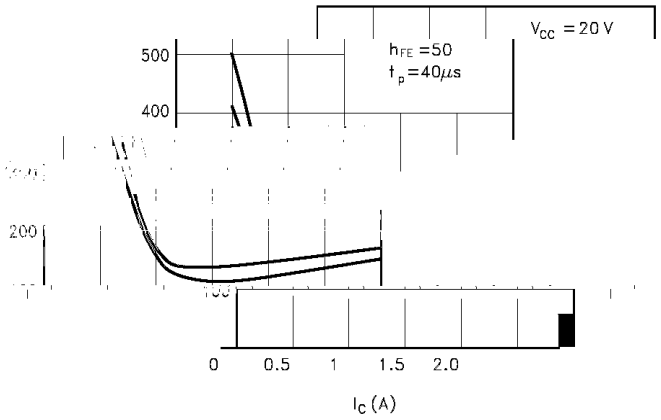


VCE(sat)-Ic

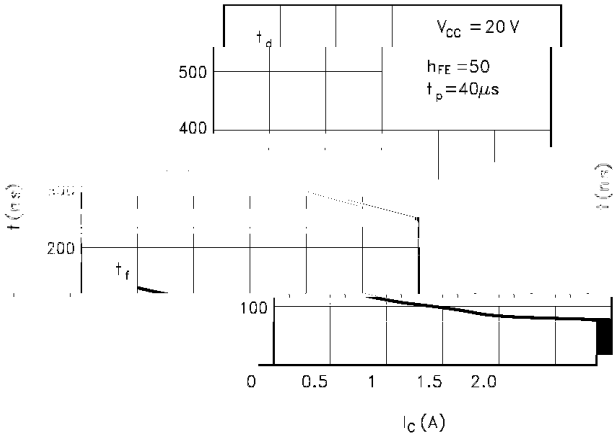




f-Ic

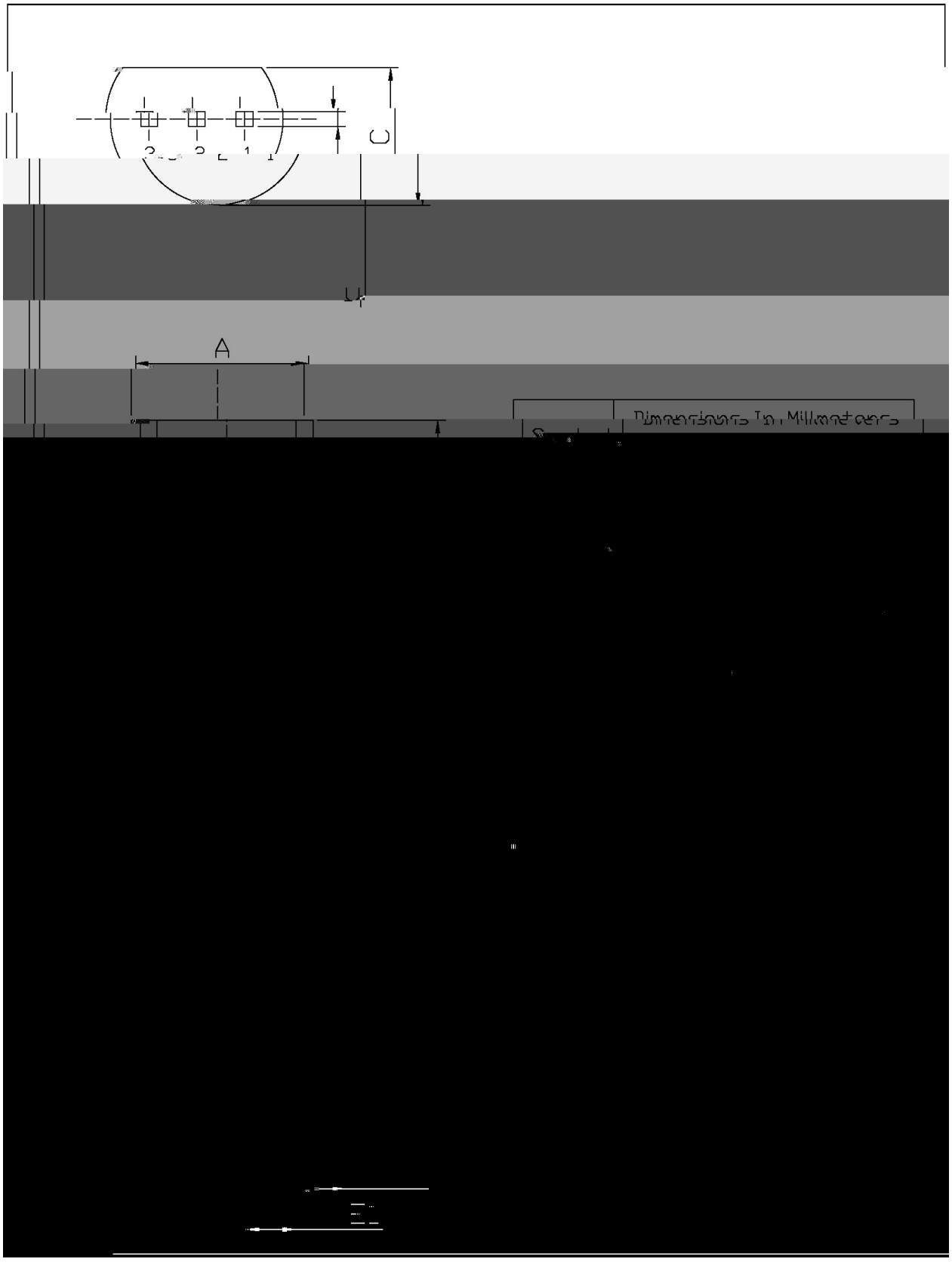


f-Ic

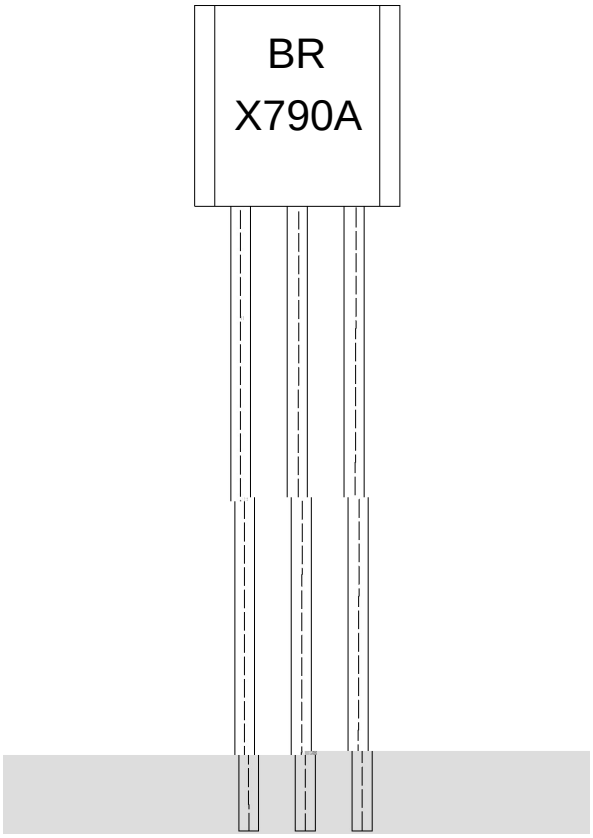


/ Package Dimensions

TO-92 Unit: mm



/ Marking Instructions



BR:

X790A

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Note:

BR:	Company Code.
X790A:	Product Type.
****:	Lot No. Code,code change with Lot No.